

P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

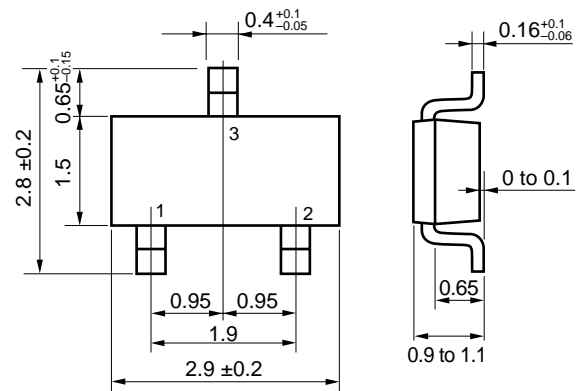
The 2SJ625 is a switching device which can be driven directly by a 1.8 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 1.8 V drive available
- Low on-state resistance
 - $R_{DS(on)1} = 113 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = -4.5 \text{ V}$, $I_D = -1.5 \text{ A}$)
 - $R_{DS(on)2} = 171 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = -2.5 \text{ V}$, $I_D = -1.5 \text{ A}$)
 - $R_{DS(on)3} = 314 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = -1.8 \text{ V}$, $I_D = -1.0 \text{ A}$)

PACKAGE DRAWING (Unit: mm)



1: Gate
2: Source
3: Drain

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ625	SC-96 (Mini Mold Thin Type)

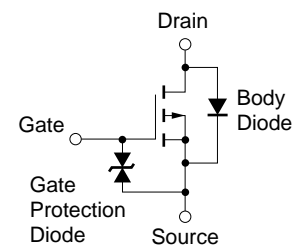
Marking: XM

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	-20	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 8.0	V
Drain Current (DC) ($T_A = 25^\circ\text{C}$)	$I_{D(DC)}$	± 3.0	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 12	A
Total Power Dissipation	P_{T1}	0.2	W
Total Power Dissipation ^{Note2}	P_{T2}	1.25	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

- Notes 1.** $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$
2. Mounted on FR-4 board, $t \leq 5 \text{ sec.}$

EQUIVALENT CIRCUIT



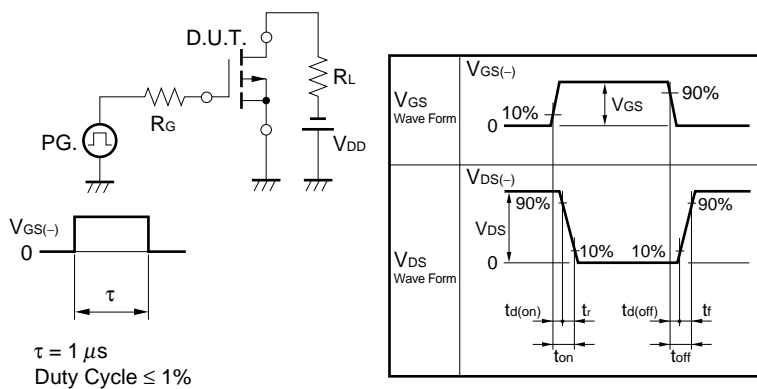
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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 Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

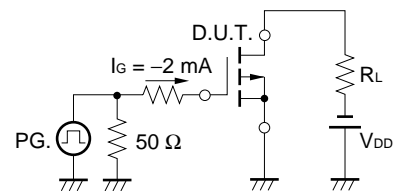
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±8.0 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1.0 mA	-0.45	-0.75	-1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10 V, I _D = -1.5 A	2.0	4.9		S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = -4.5 V, I _D = -1.5 A		90	113	mΩ
	R _{DS(on)2}	V _{GS} = -2.5 V, I _D = -1.5 A		128	171	mΩ
	R _{DS(on)3}	V _{GS} = -1.8 V, I _D = -1.0 A		188	314	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V		348		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		88		pF
Reverse Transfer Capacitance	C _{rss}	f = 1.0 MHz		38		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -10 V, I _D = -1.5 A		39		ns
Rise Time	t _r	V _{GS} = -4.0 V		190		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		220		ns
Fall Time	t _f			250		ns
Total Gate Charge	Q _G	V _{DD} = -16 V		2.6		nC
Gate to Source Charge	Q _{GS}	V _{GS} = -4.0 V		0.8		nC
Gate to Drain Charge	Q _{GD}	I _D = -3.0 A		0.9		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 3.0 A, V _{GS} = 0 V		0.89		V

TEST CIRCUIT 1 SWITCHING TIME

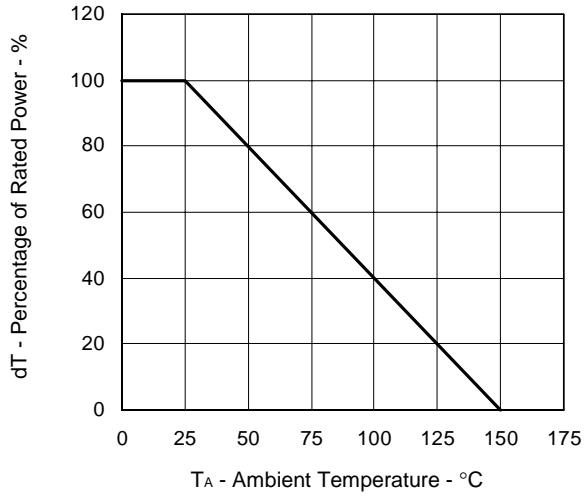


TEST CIRCUIT 2 GATE CHARGE

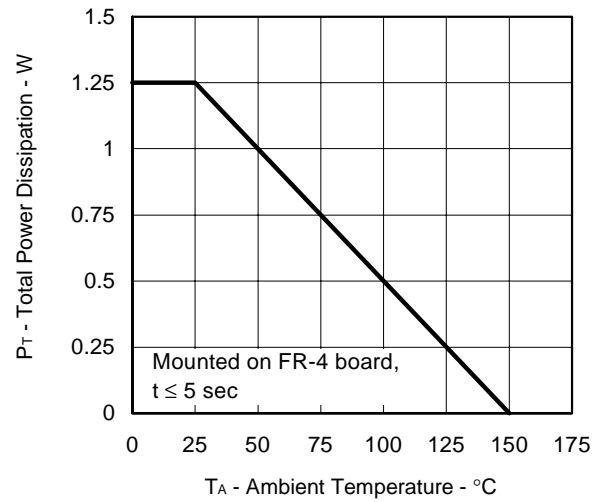


TYPICAL CHARACTERISTICS (T_A = 25°C)

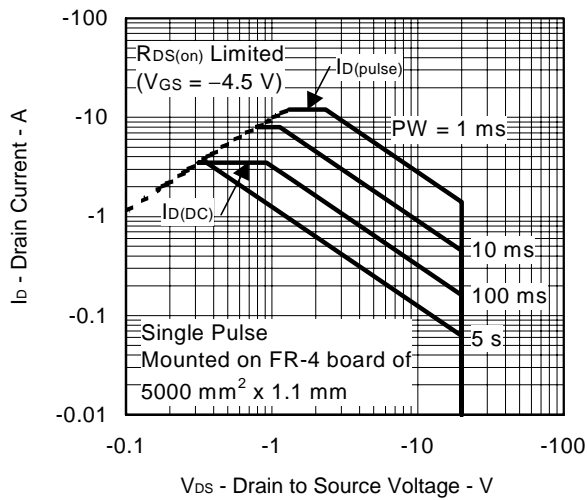
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



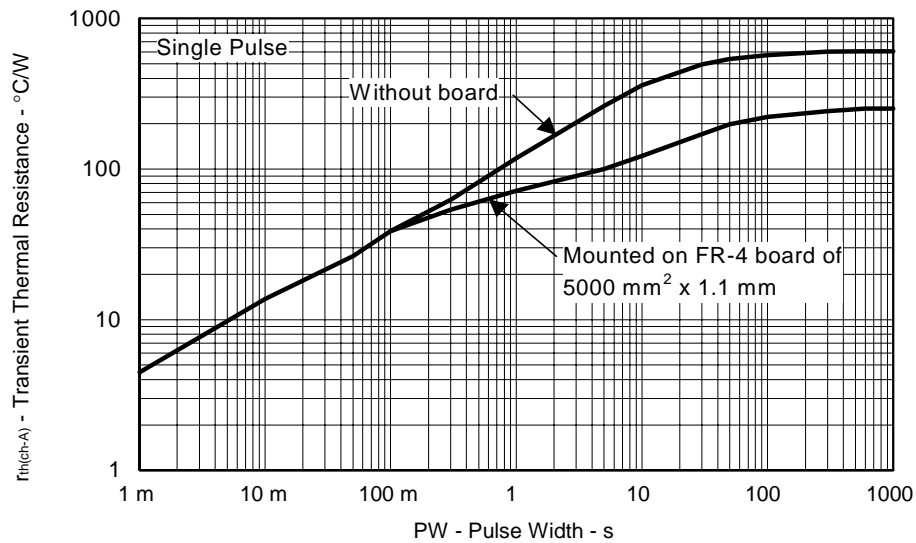
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



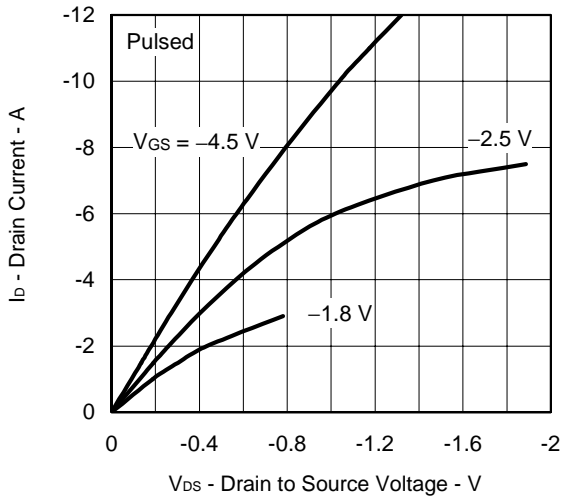
FORWARD BIAS SAFE OPERATING AREA



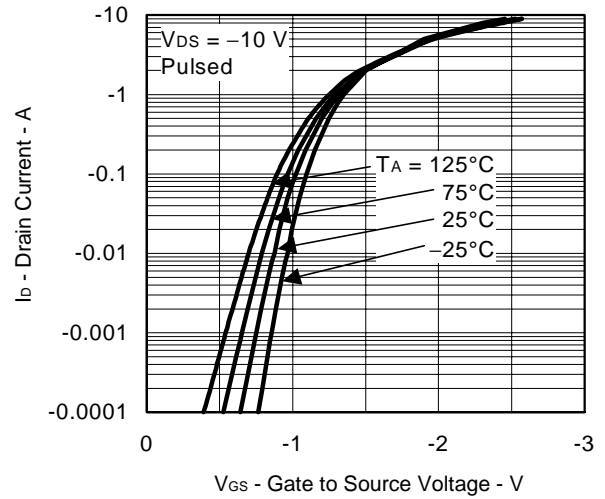
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



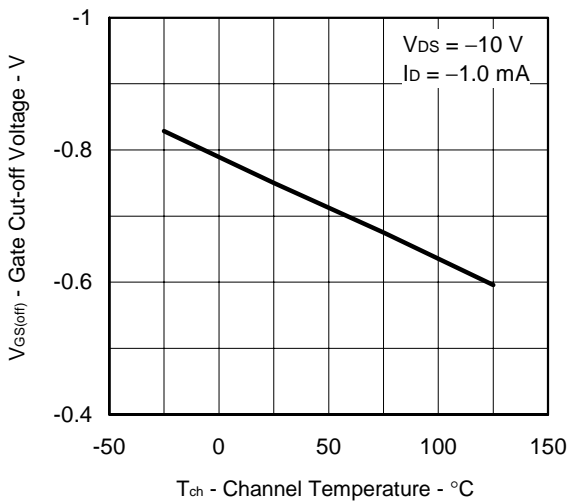
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



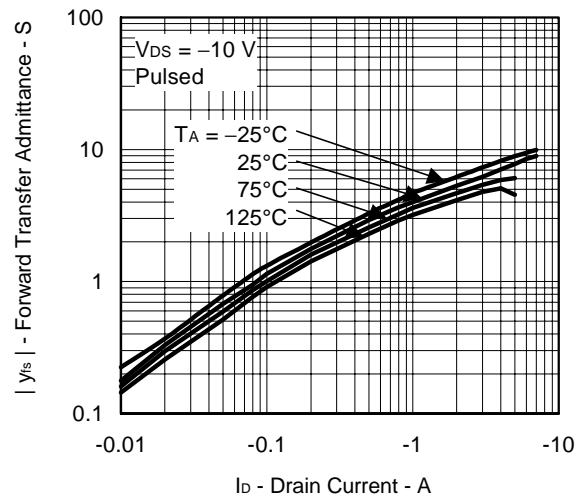
FORWARD TRANSFER CHARACTERISTICS



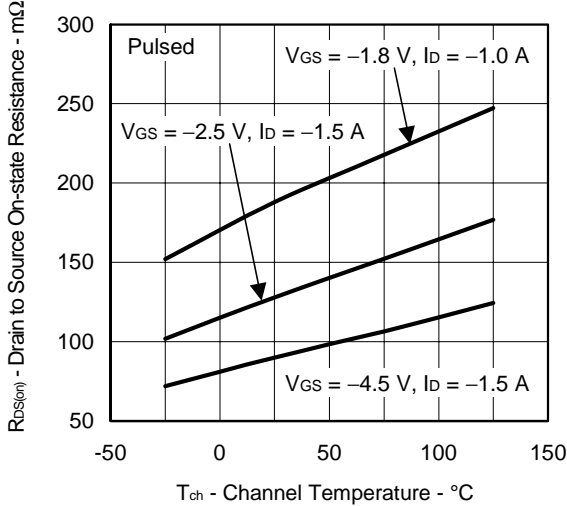
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



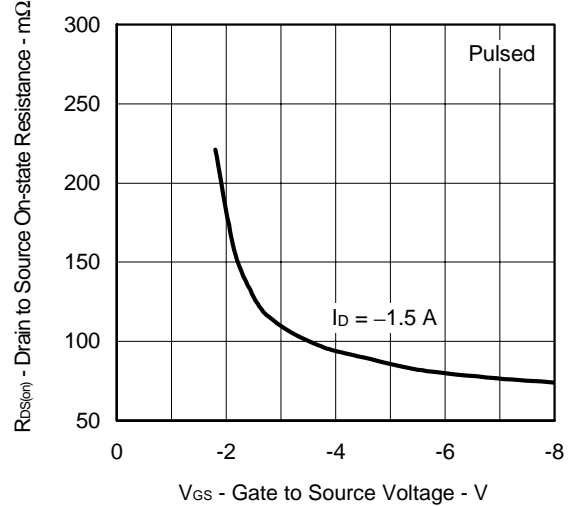
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

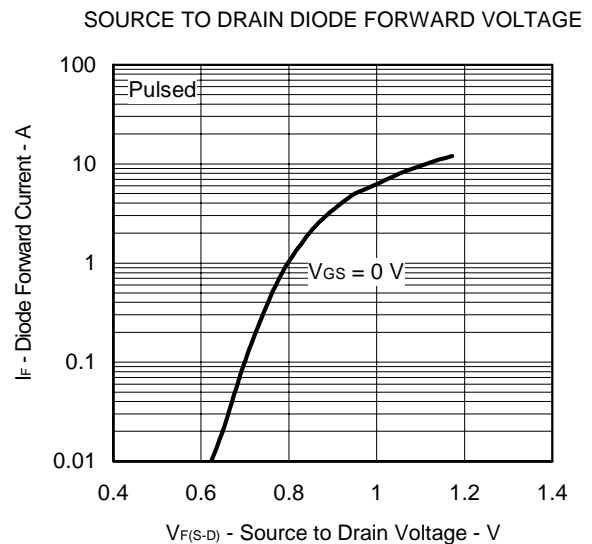
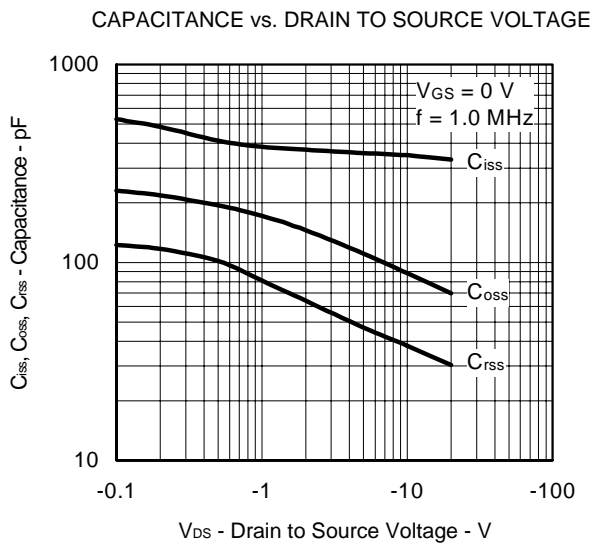
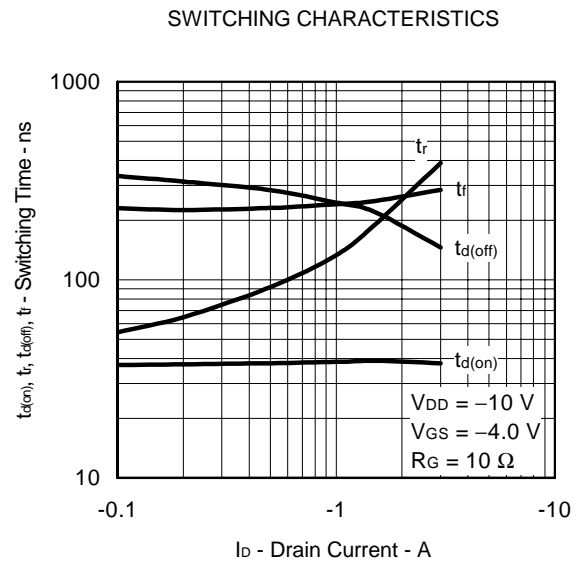
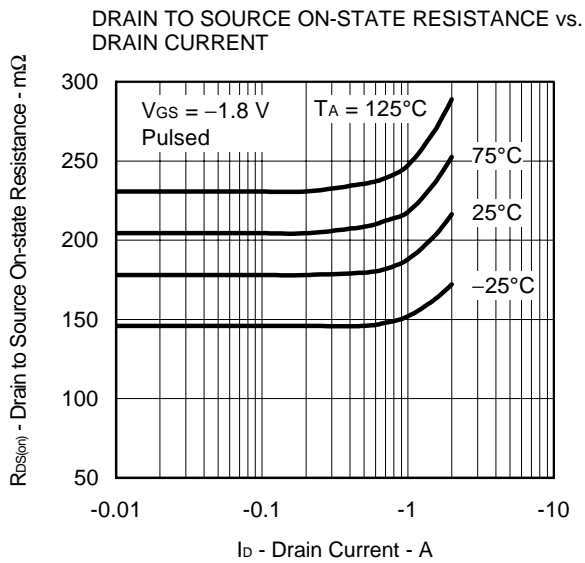
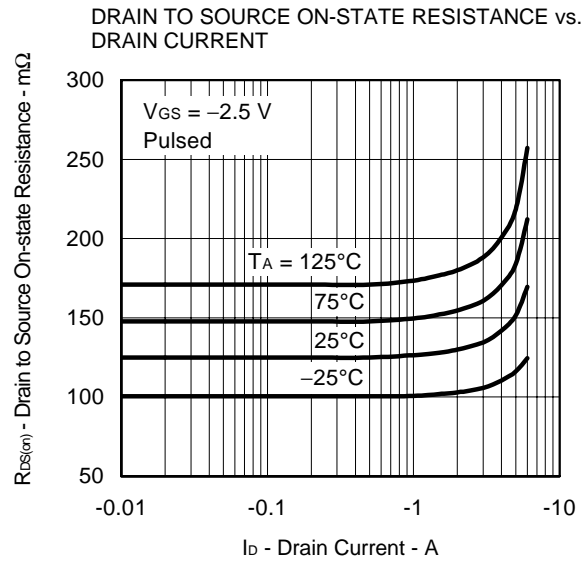
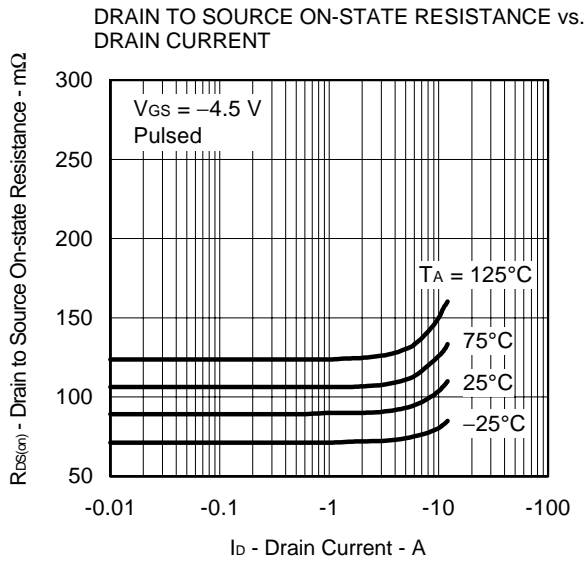


DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

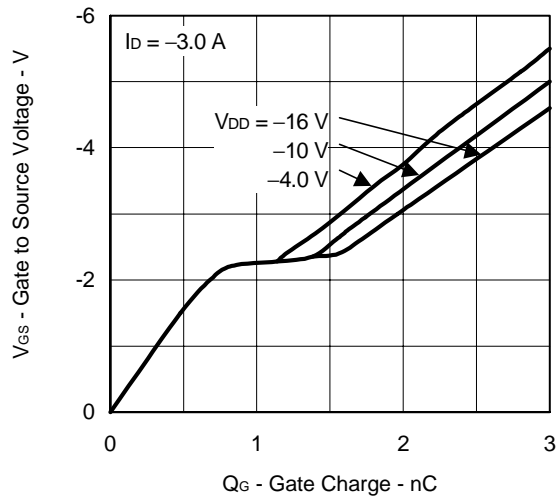


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE





DYNAMIC INPUT/OUTPUT CHARACTERISTICS



[MEMO]

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